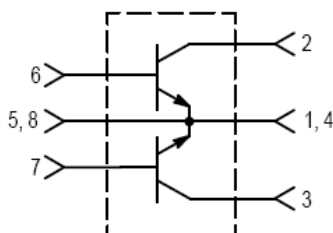


The RF Line Controlled “Q” Broadband Power Transistor 100W, 30 to 500MHz, 28V

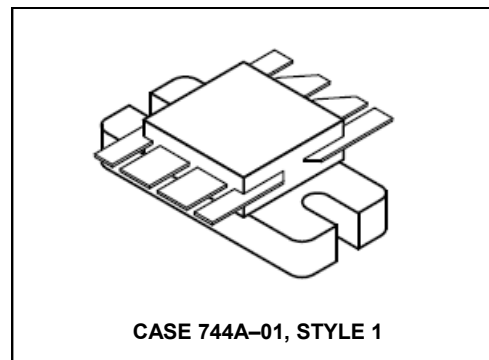
Rev. V1

Designed primarily for wideband large-signal output and driver amplifier stages in the 30 to 500 MHz frequency range.

- Specified 28 V, 500 MHz characteristics —
Output power = 100 W
Typical gain = 9.5 dB (Class AB); 8.5 dB (Class C)
Efficiency = 55% (typ.)
- Built-in input impedance matching networks for broadband operation
- Push-pull configuration reduces even numbered harmonics
- Gold metallization system for high reliability
- 100% tested for load mismatch



Product Image



The MRF393 is two transistors in a single package with separate base and collector leads and emitters common. This arrangement provides the designer with a space saving device capable of operation in a push-pull configuration.

PUSH-PULL TRANSISTORS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	16	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	270 1.54	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	$^\circ\text{C/W}$

NOTE:

- This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF push-pull amplifier.

The RF Line Controlled “Q” Broadband Power Transistor

100W, 30 to 500MHz, 28V

Rev. V1

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS (1)

Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 5.0\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	5.0	mAdc

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	—	100	—
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DYNAMIC CHARACTERISTICS (1)

Output Capacitance ($V_{CB} = 28\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	40	75	95	pF
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FUNCTIONAL TESTS (2) — See Figure 1

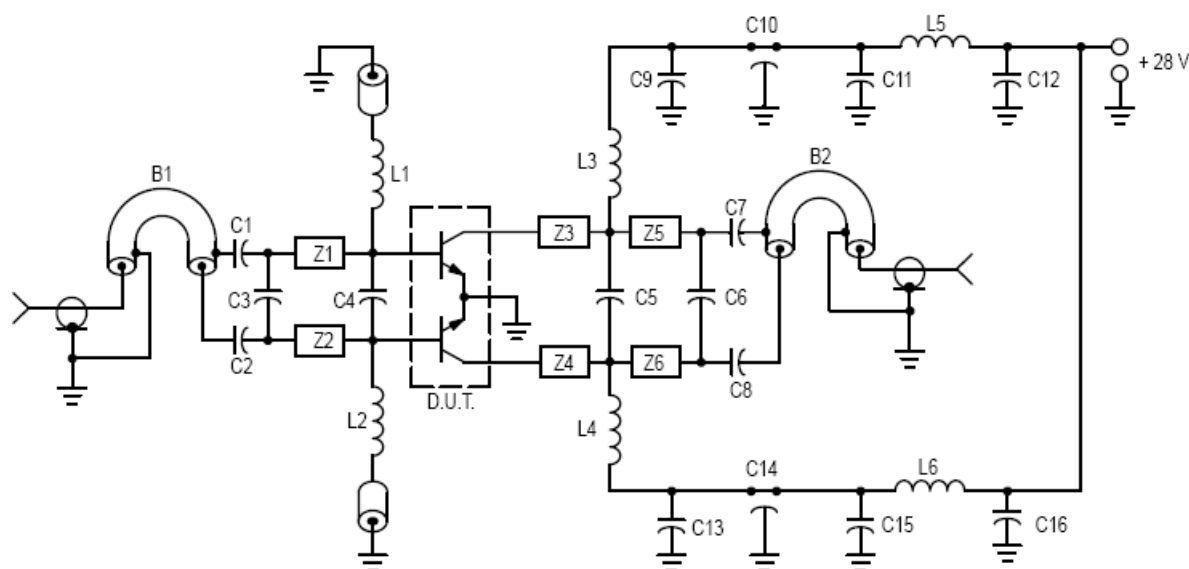
Common–Emitter Amplifier Power Gain ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$)	G_{pe}	7.5	8.5	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$)	η	50	55	—	%
Load Mismatch ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$, $VSWR = 30:1$, all phase angles)	ψ	No Degradation in Output Power			

NOTES:

1. Each transistor chip measured separately.
2. Both transistor chips operating in push–pull amplifier.

The RF Line Controlled “Q” Broadband Power Transistor 100W, 30 to 500MHz, 28V

Rev. V1



C1, C2, C7, C8 — 240 pF 100 mil Chip Cap
C3 — 15 pF 100 mil Chip Cap
C4 — 24 pF 100 mil Chip Cap
C5 — 33 pF 100 mil Chip Cap
C6 — 12 pF 100 mil Chip Cap
C9, C13 — 1000 pF 100 mil Chip Cap
C10, C14 — 680 pF Feedthru Cap
C11, C15 — 0.1 μ F Ceramic Disc Cap
C12, C16 — 50 μ F 50 V

L1, L2 — 0.15 μ H Molded Choke with Ferrite Bead
L3, L4 — 2-1/2 Turns #20 AWG 0.200" ID
L5, L6 — 3-1/2 Turns #18 AWG 0.200" ID
B1, B2 — Balun 50 Ω Semi Rigid Coax, 86 mil OD, 4" Long
Z1, Z2 — 850 mil Long x 125 mil W. Microstrip
Z3, Z4 — 200 mil Long x 125 mil W. Microstrip
Z5, Z6 — 800 mil Long x 125 mil W. Microstrip
Board Material — 0.0325" Teflon-Fiberglass, $\epsilon_r = 2.56$,
1 oz. Copper Clad both sides.

Figure 1. 500 MHz Test Fixture

The RF Line Controlled "Q" Broadband Power Transistor 100W, 30 to 500MHz, 28V

Rev. V1

CLASS C

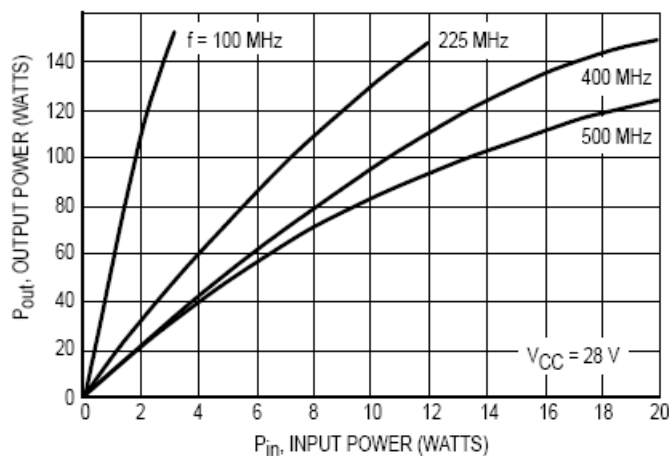


Figure 2. Output Power versus Input Power

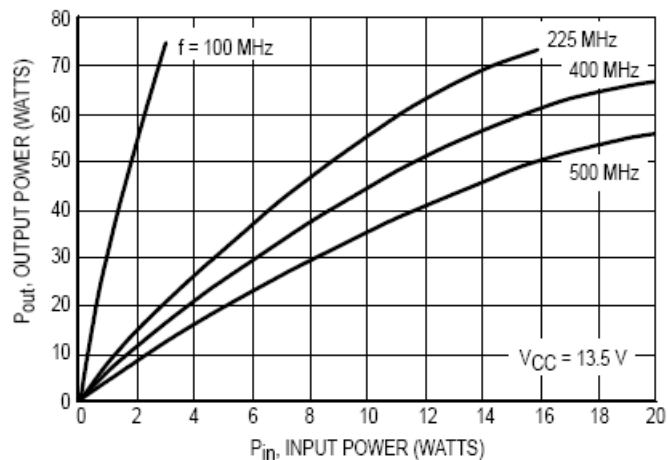


Figure 3. Output Power versus Input Power

CLASS C

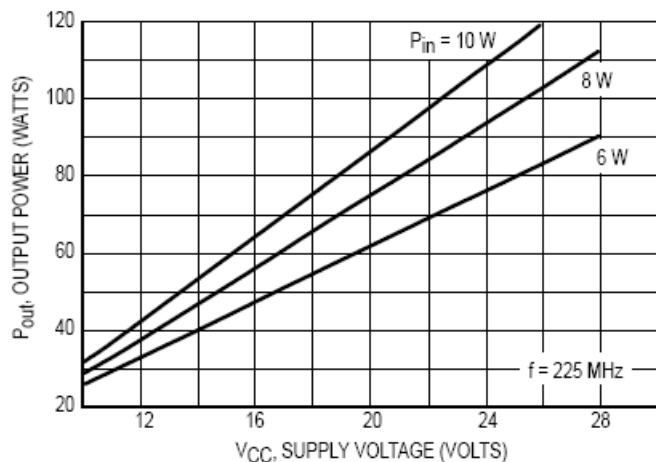


Figure 4. Output Power versus Supply Voltage

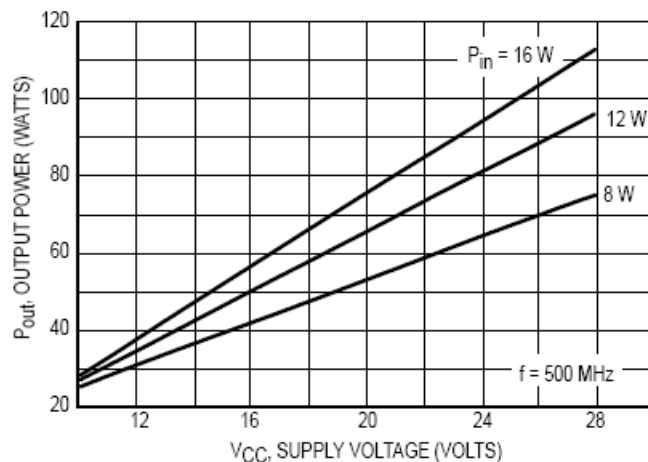
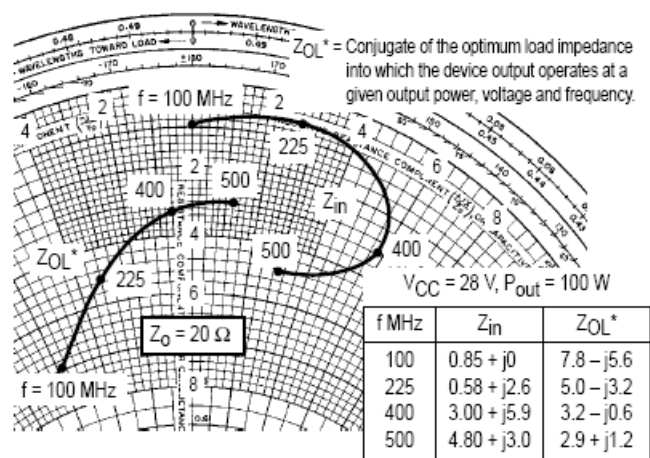


Figure 5. Output Power versus Supply Voltage

The RF Line Controlled “Q” Broadband Power Transistor 100W, 30 to 500MHz, 28V

Rev. V1



NOTE: Z_{in} & Z_{OL}^* are given from base-to-base and collector-to-collector respectively.

Figure 6. Series Equivalent Input/Output Impedance

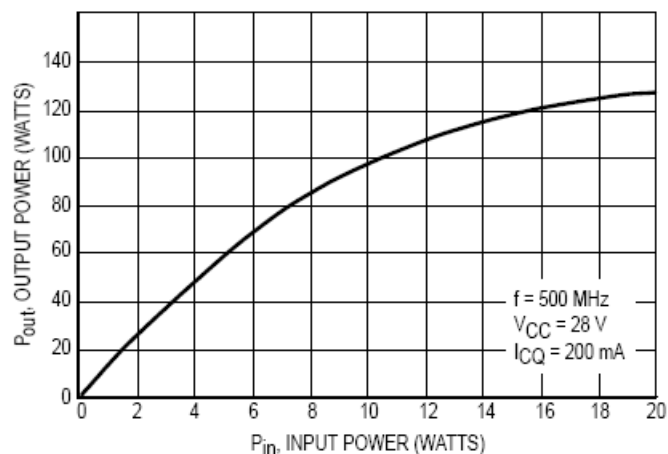
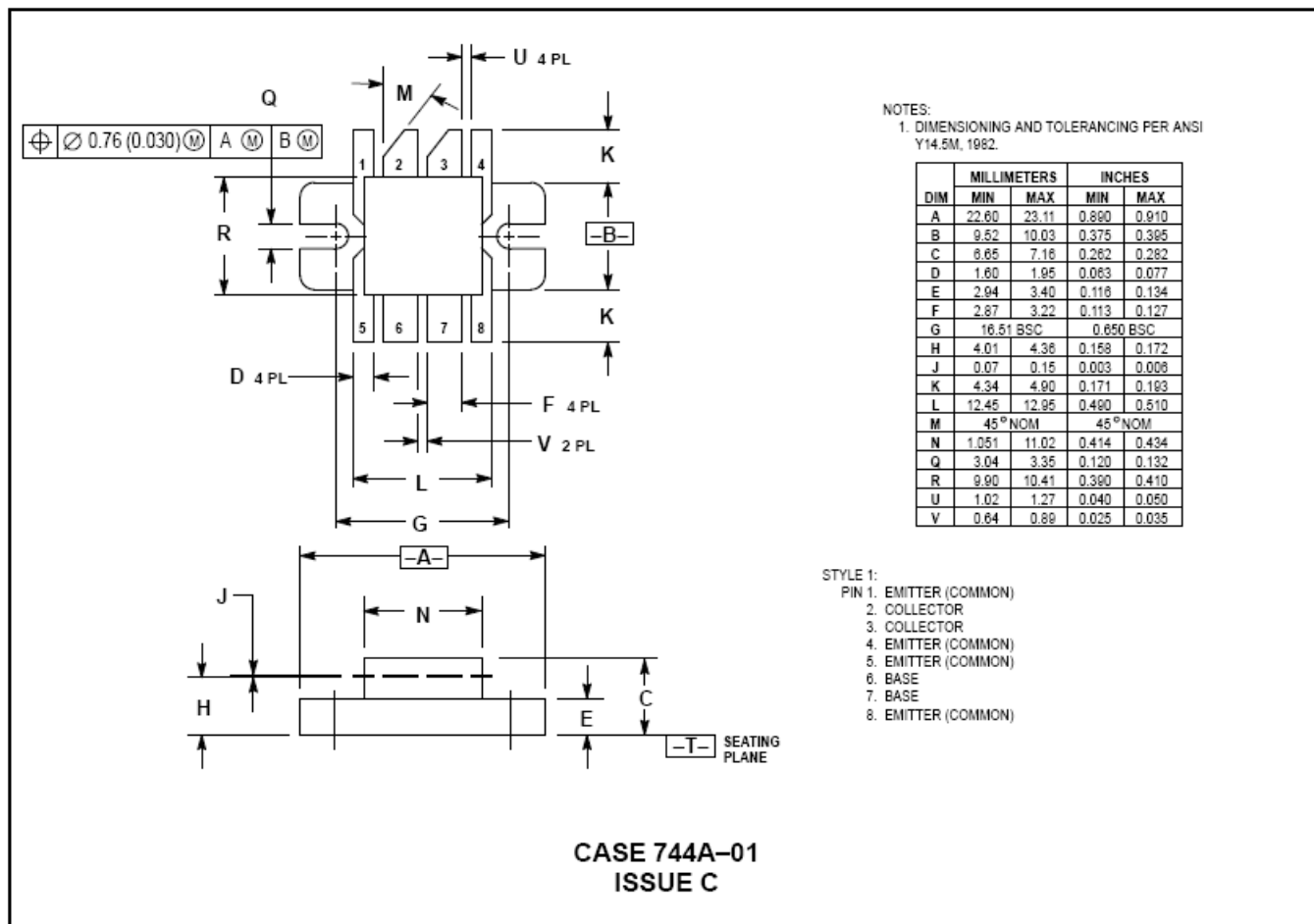


Figure 7. Class AB Output Power versus Input Power

The RF Line Controlled "Q" Broadband Power Transistor 100W, 30 to 500MHz, 28V

Rev. V1

PACKAGE DIMENSIONS



The RF Line Controlled “Q” Broadband Power Transistor 100W, 30 to 500MHz, 28V

Rev. V1

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